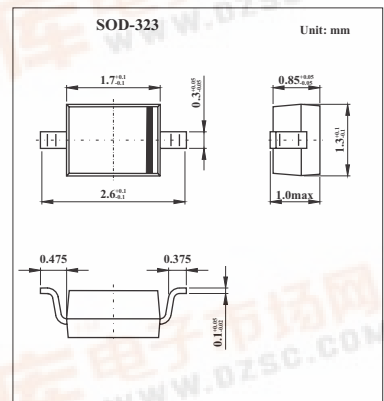


SMD Type Diodes

Silicon Epitaxial Planar Diode  
MA2ZV03

Features

- Good linearity and large capacitance-ratio in CD-VR relation
- Small series resistance  $r_D$
- S-mini type package, allowing downsizing of equipment and automatic insertion through the taping package



Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage (DC)	$V_R$	6	V
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 5\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$f = 1\text{ MHz}; V_R = 1\text{ V}$	5.2		5.8	pF
	$C_{D(4V)}$	$f = 1\text{ MHz}; V_R = 4\text{ V}$	2.1		2.58	
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		2.1		2.6	
Series resistance *	$r_s$	$V_R = 4\text{ pF}, f = 470\text{ MHz}$		1.9	0.3	$\Omega$

Note :

1. Rated input/output frequency: 470 MHz
2. \*: rf measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

Marking

Marking	7Z
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